

Notice of References Cited	Application/Control No. 10/573,793	Applicant(s)/Patent Under Reexamination TAKAYA ET AL.	
	Examiner Tuan N. Quach	Art Unit 2893	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Takaya, H., et al., Floating Island and Thick Bottom Oxide Trench Gate MOSFET (FITMOS), Proceedings of the 17th International Symposium on Power Semiconductor Devices & IC's, May 23-26, 2005, pp. 43- 46.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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